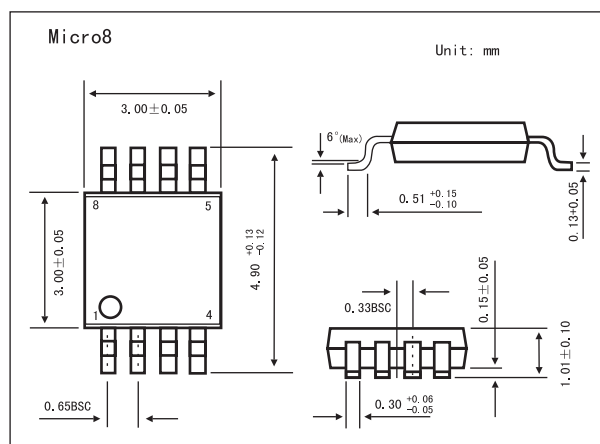
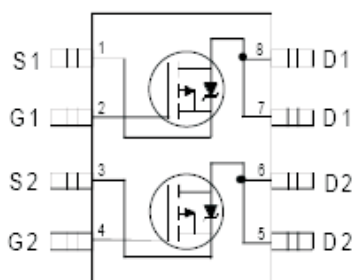


HEXFET[®] Power MOSFET

KRF7555

■ Features

- Trench Technology
- Ultra Low On-Resistance
- Dual P-Channel MOSFET
- Very Small SOIC Package
- Low Profile (<1.1mm)
- Available in Tape & Reel



■ Absolute Maximum Ratings $T_A = 25^{\circ}\text{C}$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-20	
Continuous Drain Current, $V_{GS} @ -4.5V @ T_A = 25^{\circ}\text{C}$	I_D	-4.3	A
Continuous Drain Current, $V_{GS} @ -4.5V @ T_A = 70^{\circ}\text{C}$	I_D	-3.4	
Pulsed Drain Current *1	I_{DM}	-34	
Power Dissipation *2 @ $T_A = 25^{\circ}\text{C}$	P_D	1.25	W
Power Dissipation *2 @ $T_A = 70^{\circ}\text{C}$		0.8	W
Linear Derating Factor		10	m W/ $^{\circ}\text{C}$
Gate-to-Source Voltage	V_{GS}	± 12	V
Single Pulse Avalanche Energy*2	E_{AS}	36	Mj
Peak Diode Recovery dv/dt *3	dv/dt	1.1	V/ns
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to + 150	$^{\circ}\text{C}$
Maximum Junction-to-Ambient *2	$R_{\theta JA}$	100	$^{\circ}\text{C}/\text{W}$

*1 Repetitive rating; pulse width limited by max. junction temperature.

*2 Surface mounted on FR-4 board, $t \leq 10\text{sec}$

*3 $I_{SD} \leq -2.0A$, $di/dt \leq -140A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^{\circ}\text{C}$

KRF7555

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250 \mu A$	-20			V
Breakdown Voltage Temp. Coefficient	$\Delta V_{(BR)DSS} / \Delta T_J$	$I_D = -1mA$, Reference to 25°C		-0.005		V/°C
Static Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -4.3A^{*1}$			0.055	Ω
		$V_{GS} = -2.5V, I_D = -3.4A^{*1}$			0.105	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.6		-1.2	V
Forward Transconductance	g_{fs}	$V_{DS} = -10V, I_D = -0.8A^{*1}$	2.5			S
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS} = -16V, V_{GS} = 0V$			-1.0	μA
		$V_{DS} = -16V, V_{GS} = 0V, T_J = 125^\circ C$			-25	
Gate-to-Source Forward Leakage	I_{GSS}	$V_{GS} = -12V$			-100	nA
Gate-to-Source Reverse Leakage		$V_{GS} = 12V$			100	
Total Gate Charge	Q_g	$I_D = -3.0A$		10	15	nC
Gate-to-Source Charge	Q_{gs}	$V_{DS} = -10V$		2.1	3.1	
Gate-to-Drain ("Miller") Charge	Q_{gd}	$V_{GS} = -5.0V$		2.5	3.7	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10V$		10		ns
Rise Time	t_r	$I_D = -2.0A$		46		
Turn-Off Delay Time	$t_{d(off)}$	$R_D = 5.0 \Omega$		60		
Fall Time	t_f	$R_g = 6.0 \Omega$		64		
Input Capacitance	C_{iss}	$V_{GS} = 0V$		1066		pF
Output Capacitance	C_{oss}	$V_{DS} = -10V$		402		
Reverse Transfer Capacitance	C_{rss}	$f = 1.0MHz$		126		
Continuous Source Current (Body Diode)	I_S	MOSFET symbol showing the integral reverse p-n junction diode. 			-1.3	A
Pulsed Source Current (Body Diode) *2	I_{SM}				-34	
Diode Forward Voltage	V_{SD}	$T_J = 25^\circ C, I_S = -1.6A, V_{GS} = 0V^{*1}$			-1.2	V
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ C, I_F = -2.5A$		54	82	ns
Reverse Recovery Charge	Q_{rr}	$di/dt = -100A/\mu s^{*1}$		41	61	nC

*1 Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$.

*2 Repetitive rating; pulse width limited by max. junction temperature.